**Product data sheet** 

## 1. General description

Ultrafast power diode in a SMB package.

### 2. Features and benefits

- · Fast switching
- SMB package
- High voltage capability
- Low forward voltage drop
- Low leakage current
- · Low thermal resistance
- · Soft recovery characteristic

## 3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- use in switching power supplies, inverters and as free wheeling diodes
- · High frequency switched-mode power supplies

## 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit		
Absolute	Absolute maximum rating					
$V_{RRM}$	repetitive peak reverse voltage		600	V		
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; square-wave pulse; $T_{lead} \le$ 158 °C; Fig. 1; Fig. 2; Fig. 3	1	Α		
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>lead</sub> ≤ 158 °C; square-wave pulse	2	Α		
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	35	A		
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	38	А		

Ultrafast power diode

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		v 14 A
2	A	anode	1 2	K — A 001aaa020

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
MURS160B	SMB	MURS160BJ	Reel	3000	SMBS	25-May-2017

# 7. Marking

### Table 4. Marking codes

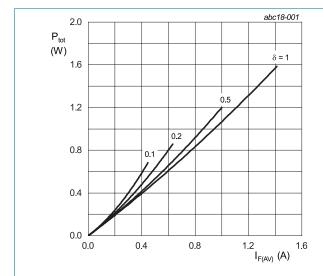
Type number	Marking codes
MURS160B	160B

## 8. Limiting values

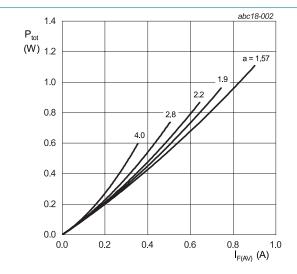
**Table 5. Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		600	V
$V_{\text{RWM}}$	crest working reverse voltage		600	V
$V_R$	reverse voltage	DC	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; square-wave pulse; T <sub>lead</sub> ≤ 158 °C; Fig. 1; Fig. 2; Fig. 3	1	Α
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>lead</sub> ≤ 158 °C; square-wave pulse	2	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	35	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	38	Α
T <sub>stg</sub>	storage temperature		-65 to 175	°C
T <sub>j</sub>	junction temperature		175	°C



$$\begin{split} & |_{\text{F(AV)}} = |_{\text{F(RMS)}} \times \sqrt{\delta} \\ & |_{\text{O}} = 0.934 \text{ V; R}_{\text{s}} = 0.1331 \text{ }\Omega \end{split}$$
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

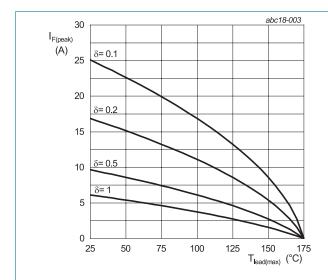


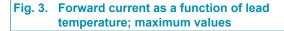
a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 0.934 V;  $R_s$  = 0.1331  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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**Ultrafast power diode** 





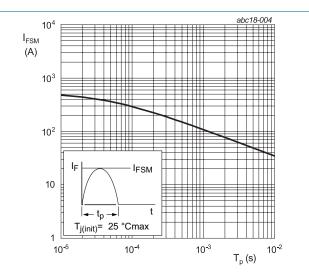


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

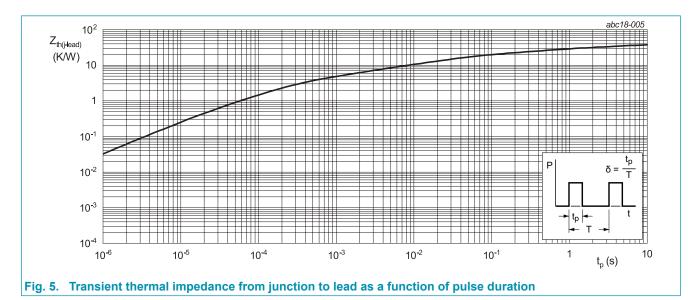
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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

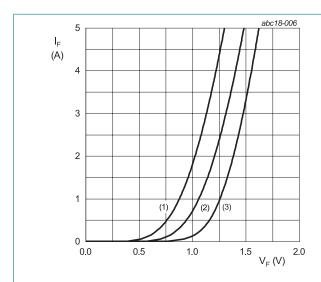
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	<u>Fig. 5</u>	-	-	14	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	115	-	K/W



## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
$V_{F}$	forward voltage	I <sub>F</sub> = 1 A; T <sub>j</sub> = 25 °C	-	-	1.25	V
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 150 °C	-	-	1.05	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	5	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	150	μA
Dynamic	characteristics					
Q <sub>r</sub>	reverse charge	$I_F = 1 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A/us}$ ; $T_J = 25 ^{\circ}\text{C}$ ; Fig. 7	-	45	-	nC
		I <sub>F</sub> = 1 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 200 A/us; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	81	-	nC
t <sub>rr</sub> reverse	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/us};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	40	75	ns
		$I_F = 1 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A/us}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	31	-	ns
		$I_F = 1 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 200 \text{ A/us}$ ; $T_j = 125 \text{ °C}$ ; Fig. 7	-	46	-	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(max)} = 0.25 \text{ A};$ $T_j = 25 ^{\circ}\text{C}; \text{ Step recovery}$	-	-	40	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/us};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	2.9	-	А
		I <sub>F</sub> = 1 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 200 A/us; T <sub>i</sub> = 125 °C; <u>Fig. 7</u>	-	3.5	-	Α



 $\begin{array}{l} V_o=0.934~V;~R_s=0.1331~\Omega\\ (1)~T_j=150~^{\circ}C;~typical~values\\ (2)~T_j=150~^{\circ}C;~maximum~values\\ (3)~T_j=25~^{\circ}C;~maximum~values \end{array}$ 

Fig. 6. Forward current as a function of forward voltage

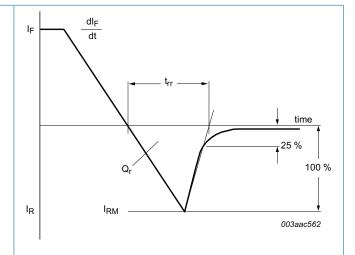
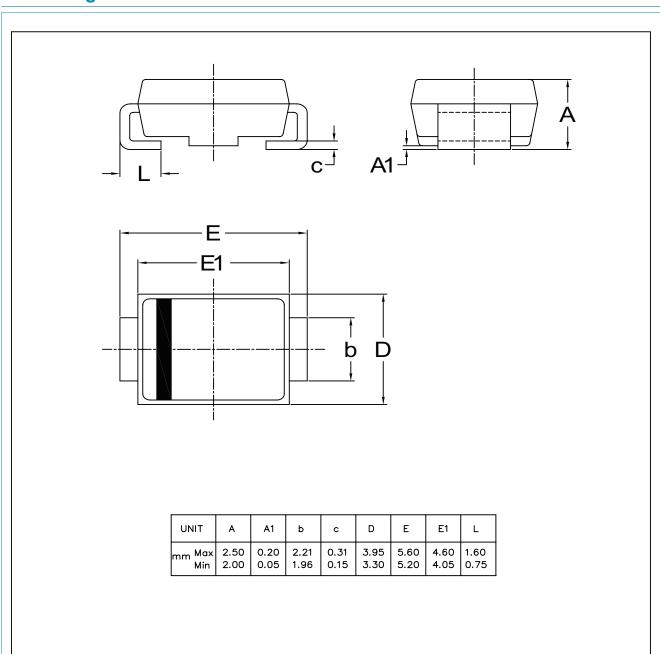


Fig. 7. Reverse recovery definitions; ramp recovery

# 11. Package outline



Remark: Dimensions D and E1 do not include mold flash.

### Ultrafast power diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.ween-semi.com">http://www.ween-semi.com</a>.

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